

1, and claims 2-4 by their dependencies. Accordingly, Applicants submit that claims 1-4 are in condition for allowance.

Claims 5-7 were rejected under 35 U.S.C. § 103(a) as being unpatentable over Kenichi in view of Applicants admitted prior art (AAPA). In particular, it was admitted that Kenichi fails to show a memory cell. To make up for this deficiency, it was asserted that the AAPA teaches a memory cell, and therefore, that it would have been obvious to one skilled in the art provide the first and second semiconductor elements of Kenichi to include the teachings of the AAPA in order to derive the present invention. Applicants respectfully submit that claims 5-7 recite subject matter not taught or suggested by any combination of the cited prior art.

As described above, in Kenichi, the concentration of the impurity in the n-well 6 is higher than the concentration of the impurity in the n-type substrate 1. In contrast, claim 1 requires that the concentration of an impurity in the semiconductor region of the first conduction type is equal to the concentration of an impurity in the semi-conductor substrate. Since claim 5-7 depend from claim 1, it would not have been obvious to one of ordinary skill in the art at the time the invention was made to combine the teaching of Kenichi with the AAPA, since the combination thereof would still fail to provide all the requirements of claims 5-7. Accordingly, Applicants submit that claims 5-7 are in condition for allowance.

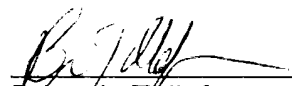
In view of the above remarks, the Applicants respectfully submit that each of claims 1-7 recite subject matter which is neither disclosed nor suggested in the cited prior art. Applicants submit that this subject matter is more than sufficient to render the

claimed invention unobvious to a person of ordinary skill in the art. Applicants therefore request that each of 1-7 be found allowable, and this application passed to issue.

If for any reason the Examiner determines that the application is not now in condition for allowance, it is respectfully requested that the Examiner contact, by telephone, the Applicants' undersigned attorney at the indicated telephone number to arrange for an interview to expedite the disposition of this application.

In the event this paper is not timely filed, the Applicants respectfully petitions for an appropriate extension of time. Any fees for such an extension together with any additional fees may be charged to Counsel's Deposit Account No. 01-2300.

Respectfully submitted,



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Enclosures: Declaration under 37 C.F.R. § 1.132

MARKED-UP AMENDMENT TO CLAIM 1

1. (Three times amended) A semiconductor device comprising:
- a lightly doped semiconductor substrate of a first conduction type;
 - a buried semiconductor layer of a second conduction type formed in a first region of the semiconductor substrate, spaced from a surface of the semiconductor substrate;
 - a semiconductor region of the second conduction type extending from the surface of the semiconductor substrate to a peripheral portion of the buried semiconductor layer; and
 - a semiconductor region of the first conduction type formed in the semiconductor substrate surrounded by the buried semiconductor layer and the semiconductor region of the second conduction type,
- wherein a concentration of an impurity in the semiconductor region of the first conduction type is [substantially] equally to a concentration of an impurity in the semiconductor substrate.